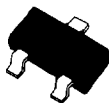


CMPTA27

SILICON DARLINGTON TRANSISTOR



SOT-23 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPTA27 type is a Silicon Darlington Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain.

Marking Code is FG.

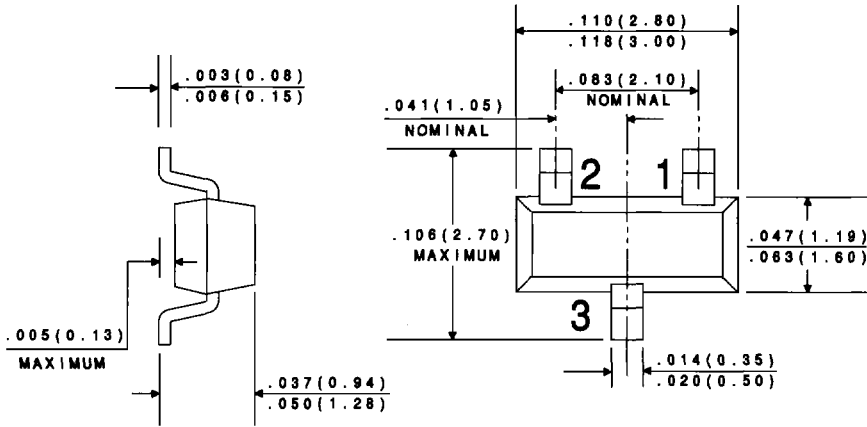
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CES}	60	V
Emitter-Base Voltage	V_{EBO}	10	V
Collector Current	I_C	500	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}	357	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CES}	$V_{CE}=50\text{V}$		500	nA
I_{CBO}	$V_{CB}=50\text{V}$		100	nA
I_{EBO}	$V_{BE}=10\text{V}$		100	nA
BV_{CES}	$I_C=100\mu\text{A}$	60		V
BV_{CBO}	$I_C=100\mu\text{A}$	60		V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=0.1\text{mA}$		1.5	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$		2.0	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	10,000		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$	10,000		
f_T	$V_{CE}=5.0\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	125		MHz

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

DATA
SHEET

R2